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10/578,835	05/10/2006	Toshio Goto	Q78632	3740
23373 7590 11/19/2009 SUGHRUE MION, PLLC 2100 PENNSYLVANIA AVENUE, N.W. SUITE 800 WASHINGTON, DC 20037				
EXAMINER MCDONALD, RODNEY GLENN				
ART UNIT		PAPER NUMBER		
1795				
NOTIFICATION DATE		DELIVERY MODE		
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

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Office Action Summary

Application No.

10/578,835

Applicant(s)

GOTO ET AL.

Examiner

Rodney G. McDonald

Art Unit

1795

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☐ Responsive to communication(s) filed on ____.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-12 is/are pending in the application.
- 4a) Of the above claim(s) ____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) ____ is/are allowed.
- 6) ☒ Claim(s) 1-12 is/are rejected.
- 7) ☐ Claim(s) ____ is/are objected to.
- 8) ☐ Claim(s) ____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on ____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. ____.
 3. ☒ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☒ Notice of Draftperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (FTO/S3/P)
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date: ____
- 5) ☐ Notice of Informal Patent Application
- 6) ☐ Other: ____
- Paper No(s)/Mail Date 5/10/06, 8/8/06

DETAILED ACTION

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-9 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1, line 6, is indefinite because "high" lacks basis for comparison.

Claim 1, line 8, is indefinite because the phrase "high purity" lacks basis for comparison.

Claim 5, line 6, is indefinite because "high" lacks basis for comparison.

Claim 8, line 2, is indefinite because the phrase "high purity" lacks basis for comparison.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 2 and 8 are rejected under 35 U.S.C. 102(b) as being anticipated by Mori et al. (U.S. Pat. 6,136,214).

Regarding claim 1, Mori et al. teach a method of generating radicals. (Column 3 lines 3-14) Mori et al. teach feeding F₂ gas or a mixed gas of F₂ gas and an inert gas

into a chamber of which the inside is provided with a carbon material. (Column 3 lines 3-14; Column 8 lines 54-63) Mori et al. teach supplying a carbon atom from the carbon material by applying a target bias voltage to the carbon material. (Column 3 lines 3-14) Mori et al. generate high density radicals. (Column 7 lines 23-27) The bias voltage is not more than 600 V applied to the carbon material to selectively form CF_3 radical and thereby high purity CF_3 radical is generated. (Column 6 lines 66-7; Column 7 lines 1-7)

Regarding claim 2, Mori et al. teach the carbon atom is generated by magnetron sputtering of the carbon material. (Column 6 lines 18-19; Column 5 lines 31-33)

Regarding claim 8, Mori et al. teach a method for etching a silicon oxide film comprising etching a silicon oxide film using high purity Cl_3 radical generated by the method for generating radicals. (Column 3 lines 3-14)

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to

consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 3 and 4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mori et al. (U.S. Pat. 6,136,214) in view of Ohmi (U.S. Pat. 5,272,417) or Celestino et al. (U.S. Pat. 4,579,618) or Gorin (U.S. Pat. 4,464,223).

Mori et al. is discussed above and all is as applies above. (See Mori et al. discussed above)

The differences between Mori et al. and the present claims is that utilizing a dual frequency applied to the target electrode using a high frequency power source and a low frequency power source is not discussed (Claim 3) and the range of the target bias is not discussed (Claim 4).

.Regarding claim 3, Ohmi teach applying multiple frequencies to an electrode to control the energy of the ions. (Column 12 lines 36-68; Column 13 lines 1-2)

The motivation for utilizing the features of Ohmi is that it allows to control the energy of the ions. (Column 12 line 38)

Regarding claim 3, Celestino et al. teach applying two frequencies to an electrode using a high frequency power source and a low frequency power source. (See Abstract; Column 3 lines 21-52)

The motivation for utilizing the features of Celestino et al. is that it allows for increasing the control of the plasma ion energy. (Column 4 lines 63-68)

Regarding claim 3, Gorin teach applying two frequencies to an electrode using a high frequency power source and a low frequency power source. (Column 2 lines 58-68; Column 3 lines 1-63; Column 4 lines 3-14)

The motivation for utilizing the features of Gorin is that it allows for controlling ion energy. (Column 1 lines 39-40)

Regarding claim 4, Mori et al. teach controlling voltage. Exemplified is controlling the voltage up to -150 V but one of ordinary skill could go beyond since Mori et al. recognize that this controls the relative densities of the radicals in the plasma. This optimizes for best results. (See Fig. 3; Column 6 lines 66-67; Column 7 lines 1-7)

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have modified Mori et al. by utilizing the features of Ohmi or Celestino et al. or Gorin because it allows for controlling ion energy.

Claims 5, 6 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mori et al. (U.S. Pat. 6,136,214) in view of Tanaka et al. (U.S. Pat. 6,590,179).

Regarding claims 5, 6, Mori et al. is discussed above and all is as applies above. (See Mori et al. discussed above)

Regarding claim 9, Mori et al. teach etching a film consisting essentially of a silicon oxide film and a resist using radicals containing CF₃ and CF₂ radicals generated by the method for generating radicals. The ratio of the density if the CF₃ radical to the density of CF₂ radical can be controlled to be not more than 10. (Column 13 lines 52-56; Fig. 3)

The differences between Mori et al. and the present claims is that controlling the ratio of radicals by controlling the target bias voltage applied to the carbon material while measuring the infrared absorption spectrum of radicals generated inside the chamber is not discussed (Claim 5).

Regarding controlling the ratio of radicals by controlling the target bias voltage applied to the carbon material while measuring the infrared absorption spectrum of radicals generated inside the chamber (Claim 5), Mori et al. already teach utilizing an optical emission spectrometer and feedback circuit to control the voltage to control the density of radicals produced. (Column 6 lines 41-68; Column 7 lines 1-7) Tanaka et al. teach measuring the infrared absorption spectrum in the chamber for control. (See Tanaka et al. Column 5 lines 26-39)

The motivation for utilizing the features of Tanaka et al. is that it allows for providing means for monitoring a plasma apparatus. (See Tanaka et al. Column 2 line 44)

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have modified Mori et al. by utilizing the features of Tanaka et al. because it allows for providing means for monitoring the plasma.

Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Mori et al. in view of Tanaka et al. as applied to claims 5, 6 and 9 above, and further in view of Ohmi (U.S. Pat. 5,272,417) or Celestino et al. (U.S. Pat. 4,579,618) or Gorin (U.S. Pat. 4,464,223).

Mori et al. is discussed above and all is as applies above. (See Mori et al. discussed above)

The differences between Mori et al. and the present claims is that utilizing a dual frequency applied to the target electrode using a high frequency power source and a low frequency power source is not discussed (Claim 7).

.Regarding claim 7, Ohmi teach applying multiple frequencies to an electrode to control the energy of the ions. (Column 12 lines 36-68; Column 13 lines 1-2)

The motivation for utilizing the features of Ohmi is that it allows to control the energy of the ions. (Column 12 line 38)

Regarding claim 7, Celestino et al. teach applying two frequencies to an electrode using a high frequency power source and a low frequency power source. (See Abstract; Column 3 lines 21-52)

The motivation for utilizing the features of Celestino et al. is that it allows for increasing the control of the plasma ion energy. (Column 4 lines 63-68)

Regarding claim 7, Gorin teach applying two frequencies to an electrode using a high frequency power source and a low frequency power source. (Column 2 lines 58-68; Column 3 lines 1-63; Column 4 lines 3-14)

The motivation for utilizing the features of Gorin is that it allows for controlling ion energy. (Column 1 lines 39-40)

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have modified Mori et al. by utilizing the features of Ohmi or Celestino et al. or Gorin because it allows for controlling ion energy.

Claims 10 and 11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mori et al. (U.S. Pat. 6,136,214) in view of Ohmi (U.S. Pat. 5,272,417) or Celestino et al. (U.S. Pat. 4,579,618) or Gorin (U.S. Pat. 4,464,223) and Tanaka et al. (U.S. Pat. 6,590,179).

Mori et al. is discussed above and all is as applies above. (See Mori et al. discussed above)

The differences between Mori et al. and the present claims are that utilizing a dual frequency applied to the target electrode using a high frequency power source and a low frequency power source is not discussed (Claims 10, 11) and the chamber being connected with an infrared absorption spectrometer so that IR laser irradiated from the infrared absorption spectrometer passes through between the application electrode and counter electrode is not discussed (Claims 10, 11).

.Regarding utilizing a dual frequency applied to the target electrode using a high frequency power source and a low frequency power source (Claims 10, 11), Ohmi teach applying multiple frequencies to an electrode to control the energy of the ions. (Column 12 lines 36-68; Column 13 lines 1-2)

The motivation for utilizing the features of Ohmi is that it allows to control the energy of the ions. (Column 12 line 38)

Regarding utilizing a dual frequency applied to the target electrode using a high frequency power source and a low frequency power source (Claims 10, 11), Celestino et al. teach applying two frequencies to an electrode using a high frequency power source and a low frequency power source. (See Abstract; Column 3 lines 21-52)

The motivation for utilizing the features of Celestino et al. is that it allows for increasing the control of the plasma ion energy. (Column 4 lines 63-68)

Regarding utilizing a dual frequency applied to the target electrode using a high frequency power source and a low frequency power source (Claims 10, 11), Gorin teach applying two frequencies to an electrode using a high frequency power source and a low frequency power source. (Column 2 lines 58-68; Column 3 lines 1-63; Column 4 lines 3-14)

The motivation for utilizing the features of Gorin is that it allows for controlling ion energy. (Column 1 lines 39-40)

Regarding the chamber being connected with an infrared absorption spectrometer so that IR laser irradiated from the infrared absorption spectrometer passes through between the application electrode and counter electrode (Claims 10,11), Tanaka et al. teach measuring the infrared absorption spectrum in the chamber for control. An IR laser can be utilized. In Fig. 1 it would pass between the two electrodes. (See Tanaka et al. Column 5 lines 26-39; Fig. 1)

The motivation for utilizing the features of Tanaka et al. is that it allows for providing means for monitoring a plasma apparatus. (See Tanaka et al. Column 2 line 44)

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have modified Mori et al. by utilizing the features of Ohmi or Celestino et al. or Gorin and to have utilized the features of Tanaka et al. because it allows for controlling ion energy and for monitoring the plasma.

Claim 12 is rejected under 35 U.S.C. 103(a) as being unpatentable over Mori et al. (U.S. Pat. 6,136,214).

Mori et al. is discussed above and all is as applies above. (See Mori et al. discussed above)

The difference between Mori et al. and the present claims is that the F2 gas concentration in the mixed gas being from 0.1 to 4.0% by volume is not discussed. (Claim 12)

Regarding claim 12, in some examples Mori et al. teach the total gas flow to be 20-300 sccm, 50-500 sccm, or 100-500 sccm. SF6 is used as a fluorine gas at a flow rate of 1-10 sccm. SF6 falls within Applicant's range of volume percent. Mori et al. also recognize F2 can be used in place of SF6. Therefore F2 would also fall within Applicant's range of volume percent. (Column 8 lines 1-8; Column 8 lines 54-68; Column 13 lines 38-40; Column 15 lines 8-23)

The motivation for utilizing the features of Mori et al. is that it allows for generating an exact amount of reactive species required for etching. (Column 2 lines 66-67)

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have utilized the features of Mori et al. because it allows for generating an exact amount of reactive species required for etching.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Rodney G. McDonald whose telephone number is 571-272-1340. The examiner can normally be reached on M-Th with every Friday off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nam X. Nguyen can be reached on 571-272-1342. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Rodney G. McDonald/
Primary Examiner, Art Unit 1795

Rodney G. McDonald
Primary Examiner
Art Unit 1795

RM
November 13, 2009